

Silicon NPN Power Transistors

BUL128D

DESCRIPTION

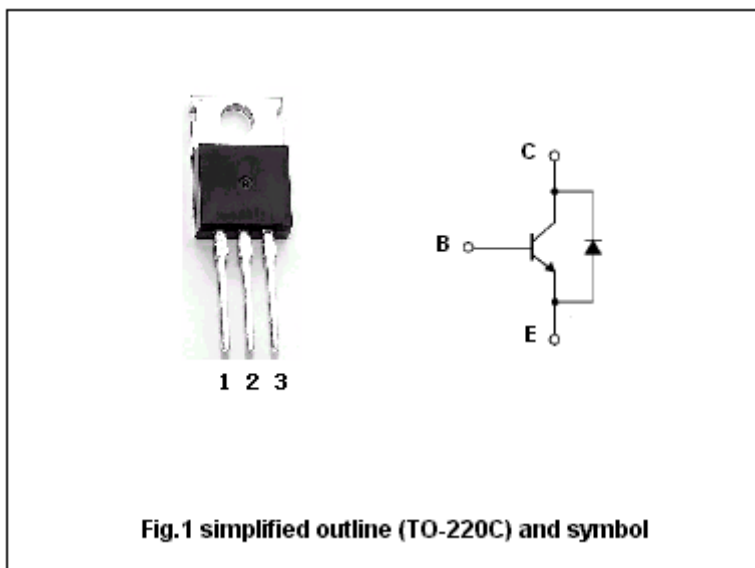
- With TO-220C package
- High voltage ,high speed
- Integrated antiparallel collector-emitter diode

APPLICATIONS

- Designed for use in lighting applications and low cost switch-mode power supplies.

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter



Absolute maximum ratings(Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	700	V
V_{CEO}	Collector-emitter voltage	Open base	400	V
V_{EBO}	Emitter-base voltage	Open collector	9	V
I_C	Collector current		4	A
I_{CM}	Collector current-Peak ($t_p < 5$ ms)		8	A
I_B	Base current		2	A
I_{BM}	Base current-Peak ($t_p < 5$ ms)		4	A
P_T	Total power dissipation	$T_C = 25^\circ C$	70	W
T_j	Junction temperature		150	$^\circ C$
T_{stg}	Storage temperature		-65~150	$^\circ C$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
R_{thj-c}	Thermal resistance from junction to case	1.78	$^\circ C/W$

Silicon NPN Power Transistors

BUL128D

CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEQ(SUS)}	Collector-emitter sustaining voltage	I _C =100mA; L=25mH	400			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =10mA; I _C =0	9			
V _{CEsat-1}	Collector-emitter saturation voltage	I _C =0.5A ; I _B =0.1A			0.7	V
V _{CEsat-2}	Collector-emitter saturation voltage	I _C =1A ; I _B =0.2A			1.0	V
V _{CEsat-3}	Collector-emitter saturation voltage	I _C =2.5A ; I _B =0.5A			1.5	V
V _{CEsat-4}	Collector-emitter saturation voltage	I _C =4A ; I _B =1A		0.5		V
V _{BEsat-1}	Base-emitter saturation voltage	I _C =0.5A ; I _B =0.1A			1.1	V
V _{BEsat-2}	Base-emitter saturation voltage	I _C =1A ; I _B =0.2A			1.2	V
V _{BEsat-3}	Base-emitter saturation voltage	I _C =2.5A ; I _B =0.5A			1.3	V
I _{CES}	Collector cut-off current	V _{CE} =700V; V _{BE} =-1.5V T _j =125°C			100 500	μ A
I _{CEO}	Collector cut-off current	V _{CE} =400V; I _B =0			250	μ A
h _{FE-1}	DC current gain	I _C =2A ; V _{CE} =5V	8		40	
h _{FE-2}	DC current gain	I _C =10mA ; V _{CE} =5V	10			
V _F	Diode forward voltage	I _C =2A			2.5	V

Switching times resistive load

t _s	Storage time	V _{CC} =250V , I _C =2A I _{B1} =-I _{B2} =0.4A; t _p =30 μ s			2.9	μ s
t _f	Fall time			0.2		μ s

Silicon NPN Power Transistors

BUL128D

PACKAGE OUTLINE

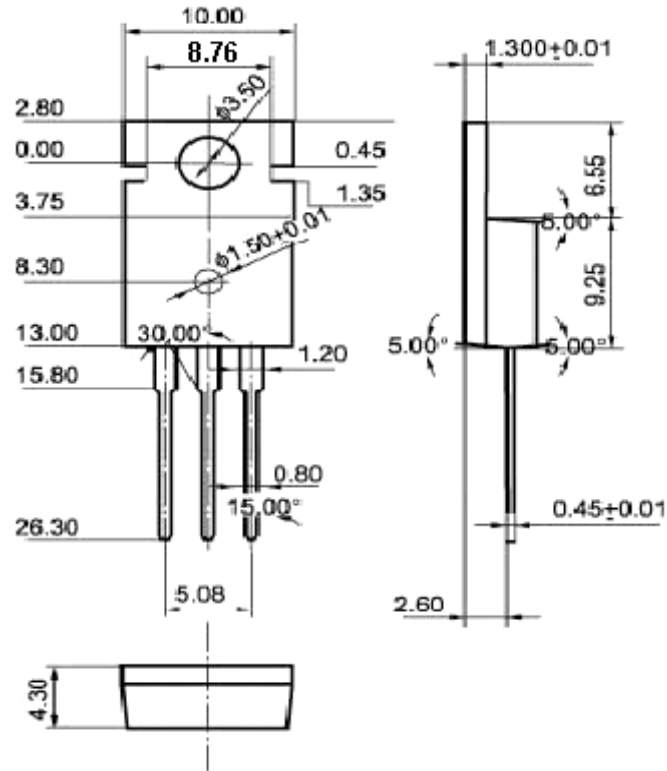


Fig.2 Outline dimensions (unindicated tolerance: 0.1mm)